

# **Schottky Diode**

 $V_{RRM} = 45 V$ 

 $I_{FAV} = 60 A$ 

 $V_F = 0.57 V$ 

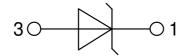
High Performance Schottky Diode Low Loss and Soft Recovery Single Diode

Part number

DSS60-0045B



Backside: cathode



## Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

# **Applications:**

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

## Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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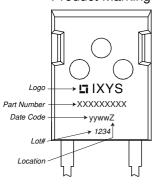


Schottky					Ratings	yp. max. Unit 45 V 45 V 60 mA 250 mA		
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V <sub>RSM</sub>	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			45	V	
V <sub>RRM</sub>	max. repetitive reverse blocking ve	oltage	$T_{VJ} = 25^{\circ}C$			45	٧	
I <sub>R</sub>	reverse current, drain current	$V_R = 45 \text{ V}$	$T_{VJ} = 25^{\circ}C$			60	mA	
		$V_R = 45 V$	$T_{VJ} = 100^{\circ}C$			250	mA	
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 60 A	$T_{VJ} = 25^{\circ}C$			0.60	V	
		$I_F = 120 A$				0.86	٧	
		$I_F = 60 \text{ A}$	T <sub>VJ</sub> = 125°C			0.57	V	
		$I_F = 120 \text{ A}$				0.87	٧	
I <sub>FAV</sub>	average forward current	T <sub>C</sub> = 105°C	$T_{VJ} = 150$ °C			60	Α	
		rectangular $d = 0.5$						
V <sub>F0</sub>	threshold voltage	an adadation only	$T_{VJ} = 150$ °C			0.27	V	
r <sub>F</sub>	slope resistance	ess calculation only				4.9	mΩ	
R <sub>thJC</sub>	thermal resistance junction to case	9				0.8	K/W	
R <sub>thCH</sub>	thermal resistance case to heatsing	nk			0.25		K/W	
P <sub>tot</sub>	total power dissipation		$T_C = 25^{\circ}C$			155	W	
I <sub>FSM</sub>	max. forward surge current	$t = 10 \text{ ms}$ ; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			600	Α	
CJ	junction capacitance	$V_R = 5V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		2.93		nF	
E <sub>AS</sub>	non-repetitive avalanche energy	I <sub>AS</sub> = 31 A L = 180 μH	$T_{VJ} = 25 ^{\circ}\text{C}$			137	mJ	
I <sub>AR</sub>	repetitive avalanche current	$V_A = 1.5 \cdot V_R$ typ. $f = 10$ kHz				3.1	Α	



Package	Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I <sub>RMS</sub>	RMS current	per terminal			70	Α	
T <sub>VJ</sub>	virtual junction temperature		-55		150	°C	
T <sub>op</sub>	operation temperature		-55		125	°C	
T <sub>stg</sub>	storage temperature		-55		150	°C	
Weight				6		g	
M <sub>D</sub>	mounting torque		0.8		1.2	Nm	
<b>F</b> <sub>c</sub>	mounting force with clip		20		120	Ν	

# **Product Marking**

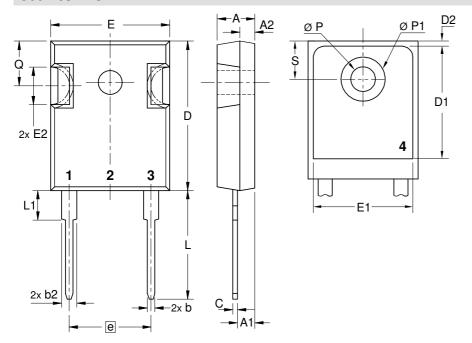


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSS60-0045B	DSS60-0045B	Tube	30	475599

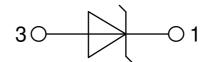
Equival	ent Circuits for	Simulation	* on die level	$T_{VJ} = 150$ °C
$I \rightarrow V_0$	$ R_o$ $-$	Schottky		
V <sub>0 max</sub>	threshold voltage	0.27		V
R <sub>0 max</sub>	slope resistance *	2.4		mΩ



# Outlines TO-247



Sym.	Inches		Millim	eter
	min.	max.	min.	max.
Α	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
е	0.430	BSC	10.92 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
ØР	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14	BSC
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
С	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39





## Schottky

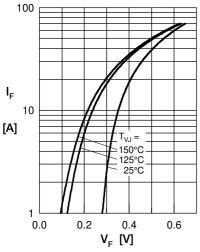


Fig. 1 Max. forward voltage drop characteristics

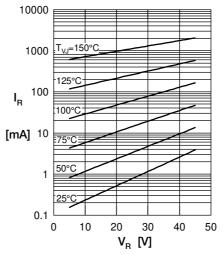


Fig. 2 Typ. reverse current  $I_R$  vs. reverse voltage  $V_R$ 

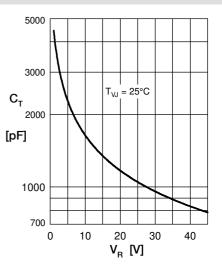


Fig. 3 Typ. junction capacitance  $C_T$  vs. reverse voltage  $V_R$ 

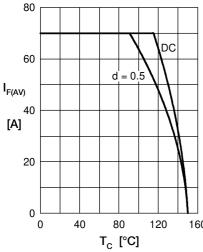


Fig. 4 Average forward current  $I_{F(AV)}$  vs. case temp.  $T_{C}$ 

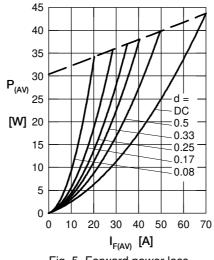


Fig. 5 Forward power loss characteristics

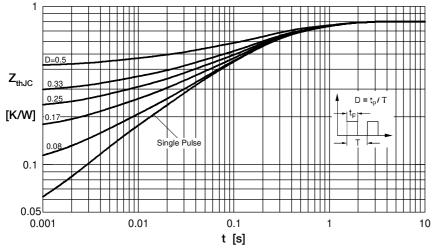


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode